

What is claimed is:

1. An electro-static chucking mechanism for chucking an object electro-statically on a chucking surface, comprising:

a stage having a dielectric block of which surface is said chucking surface, and a chucking electrode provided in said dielectric block;

a temperature controller provided with said stage for controlling temperature of said object;

a chucking power source to apply voltage to said chucking electrode so that said object is chucked;

wherein,

said chucking surface has concaves of which openings are shut by said chucked object,

a heat-exchange gas introduction system that introduces heat-exchange gas into said concaves is provided,

said concaves include a heat-exchange concave for promoting heat-exchange under increased pressure and a gas-diffusion concave for making said introduced gas diffuse to said heat-exchange concave, and

said gas-diffusion concave is deeper than said heat-exchange concave.

2. An electro-static chucking mechanism as claimed in claim 1,
wherein

said gas-diffusion concave is formed in coaxial with the
center of said stage.

3. An electro-static chucking mechanism as claimed in claim 1,
wherein;

depth of said heat-exchange concave is in the range of
1 to 20 μm .

4. An electro-static chucking mechanism as claimed in claim
1, wherein;

area of said chucking surface in contact with said
chucked object is in the range of 3 to 20 % against surface
area of said object facing to said stage.

5. An electro-static chucking mechanism as claimed in claim 1,
wherein;

cross-sectional area of said gas-diffusion concave
along said chucking surface is in the range of 5 to 30 %
against surface area of said object facing to said stage.

6. An electro-static chucking mechanism as claimed in claim 1,

wherein;

depth of said gas-diffusion concave is in the range of
50 to 1000 μm .

7. An electro-static chucking mechanism for chucking an object
electro-statically on a chucking surface, comprising:

a stage having a dielectric block of which surface is
said chucking surface, and a chucking electrode provided in
said dielectric block;

a temperature controller provided with said stage for
controlling temperature of said object;

a chucking power supply to apply voltage to said chucking
electrode to chuck said object;

wherein,

said chucking surface has a concave of which opening is
shut by said chucked object,

said stage has a gas introduction channel reaching to
said concave,

a gas introduction system that introduces heat-exchange
gas into said concave through said gas introduction channel
is provided for increasing pressure in said concave,

a lift pin for receiving and passing said object is
provided in said gas introduction channel.

8. A surface processing apparatus, comprising:

a process chamber in which a surface of an object is processed, and

an electro-static chucking mechanism for chucking said object electro-statically on a chucking surface in said process chamber,

wherein:

said mechanism comprises a stage having a dielectric block of which surface is said chucking surface, and a chucking electrode provided in said dielectric block;

a temperature controller is provided with said stage for controlling temperature of said object;

a chucking power source to apply voltage to said chucking electrode is provided so that said object is chucked;

said chucking surface has concaves of which openings are shut by said chucked object;

a heat-exchange gas introduction system that introduces heat-exchange gas into said concaves is provided;

said concaves include a heat-exchange concave for promoting heat-exchange under increased pressure and a gas-diffusion concave for making said introduced gas diffuse to said heat-exchange concave; and

said gas-diffusion concave is deeper than said heat-exchange concave.

9. A surface processing apparatus as claimed in claim 8, wherein said gas-diffusion concave is formed in coaxial with the center of said stage.

10. A surface processing apparatus as claimed in claim 8, wherein;

depth of said heat-exchange concave is in the range of 1 to 20 μm .

11. A surface processing apparatus as claimed in claim 8, wherein

area of said chucking surface in contact with said object is in the range of 3 to 20 % against surface area of said object facing to said stage.

12. A surface processing apparatus as claimed in claim 8, wherein

cross-sectional area of said gas-diffusion concave along said chucking surface is in the range of 5 to 30 % of surface area of said object facing to said stage.

13. A surface processing apparatus as claimed in claim 8,
wherein

depth of said gas-diffusion concave is in the range of
50 to 1000 μm .

14. A surface processing apparatus, comprising:

a process chamber in which a surface of an object is
processed, and

an electro-static chucking mechanism for chucking said
object electro-statically on a chucking surface in said
process chamber,

wherein:

said mechanism comprises a stage having a dielectric
block of which surface is said chucking surface, and a
chucking electrode provided in said dielectric block;

a temperature controller is provided with said stage for
controlling temperature of said object;

a chucking power source to apply voltage to said chucking
electrode is provided so that said object is chucked;

said chucking surface has a concave of which opening is
shut by said chucked object,

said stage has a gas introduction channel reaching to

said concave,

a gas introduction system that introduces heat-exchange gas into said concave through said gas introduction channel is provided for increasing pressure in said concave,

a lift pin for receiving and passing said object is provided in said gas introduction channel.